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Team Nexperia



BCV61

NPN general-purpose double transistors Rev. 04 — 18 December 2009

Product data sheet

Product profile

1.1 General description

NPN general-purpose double transistors in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

Type number	Package		PNP complement	
	NXP	JEITA		
BCV61	SOT143B -		BCV62	
BCV61A			BCV62A	
BCV61B			BCV62B	
BCV61C			BCV62C	

1.2 Features

- Low current (max. 100 mA)
- Low voltage (max. 30 V)
- Matched pairs

1.3 Applications

- Applications with working point independent of temperature
- Current mirrors

Pinning information 2.

Table 2 Pinning

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	collector TR2; base TR1 and TR2	4 3	4 3
2	collector TR1		X 1 12
3	emitter TR1		TR2
4	emitter TR2	1 2	1 2 006aaa842



NPN general-purpose double transistors

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BCV61	-	plastic surface-mounted package; 4 leads	SOT143B		
BCV61A					
BCV61B					
BCV61C					

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BCV61	1M*
BCV61A	1J*
BCV61B	1K*
BCV61C	1L*

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	istor				
V_{CBO}	collector-base voltage	open emitter	-	30	V
V_{CEO}	collector-emitter voltage	open base	-	30	V
V_{EBS}	emitter-base voltage	$V_{CE} = 0 V$	-	6	V
I_{C}	collector current		-	100	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	200	mA
Per devic	ce				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB).

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^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

^[1] Device mounted on an FR4 PCB.

7. Characteristics

Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Transist	or TR1						
I _{CBO}	collector-base cut-off current	$V_{CB} = 30 \text{ V};$ $I_{E} = 0 \text{ A}$		-	-	15	nA
		$V_{CB} = 30 \text{ V};$ $I_{E} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V};$ $I_C = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V};$ $I_{C} = 100 \mu\text{A}$		100	-	-	
		$V_{CE} = 5 \text{ V};$ $I_C = 2 \text{ mA}$		110	-	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$		-	90	250	mV
		$I_C = 100 \text{ mA};$ $I_B = 5 \text{ mA}$		-	200	600	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$	[1]	-	700	-	mV
		$I_C = 100 \text{ mA};$ $I_B = 5 \text{ mA}$	<u>[1]</u>	-	900	-	mV
V_{BE}	base-emitter voltage	$I_C = 2 \text{ mA};$ $V_{CE} = 5 \text{ V}$	[2]	580	660	700	mV
		$I_C = 10 \text{ mA};$ $V_{CE} = 5 \text{ V}$	[2]	-	-	770	mV
f _T	transition frequency	$V_{CE} = 5 \text{ V};$ $I_{C} = 10 \text{ mA};$ $f = 100 \text{ MHz}$		100	-	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V};$ $I_{E} = i_{e} = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	2.5	-	pF
NF	noise figure	$V_{CE} = 5 \text{ V};$ $I_{C} = 200 \mu\text{A};$ $R_{S} = 2 k\Omega;$ $f = 1 k\text{Hz};$ $B = 200 \text{ Hz}$		-	-	10	dB

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Table 7. Characteristics ...continued $T_i = 25$ °C unless otherwise specified.

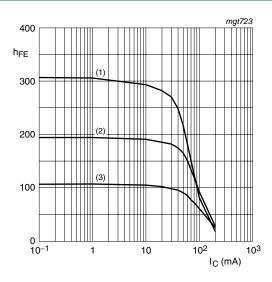
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Transist	or TR2					
V_{EBS}	emitter-base voltage	$V_{CB} = 0 \text{ V};$ $I_{E} = -250 \text{ mA}$	-	-	-1.8	V
		$V_{CB} = 0 \text{ V};$ $I_{E} = -10 \mu\text{A}$	-400	-	-	mV
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V};$ $I_{C} = 2 \text{ mA}$				
	BCV61		110	-	800	
	BCV61A		110	-	220	
	BCV61B		200	-	450	
	BCV61C		420	-	800	
Transist	ors TR1 and TR2					
I_{C1}/I_{E2}	current matching	$I_{E2} = -0.5 \text{ mA};$ $V_{CE1} = 5 \text{ V}$				
		$T_{amb} \le 25 ^{\circ}C$	0.7	-	1.3	
		T _{amb} ≤ 150 °C	0.7	-	1.3	
I _{E2}	emitter current 2	V _{CE1} = 5 V	[3]	-	-5	mA

^[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

^[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

^[3] Device, without emitter resistors, mounted on an FR4 PCB.

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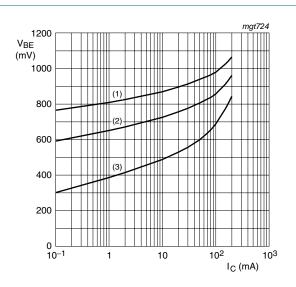
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 1. BCV61A: DC current gain as a function of collector current; typical values



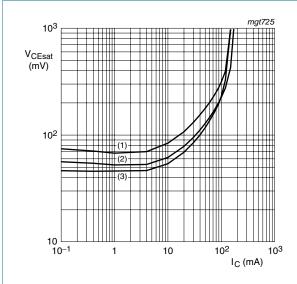
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 2. BCV61A: Base-emitter voltage as a function of collector current; typical values



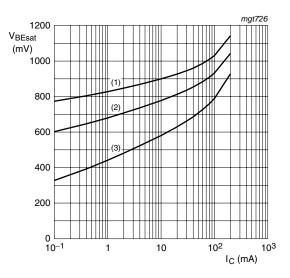
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. BCV61A: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

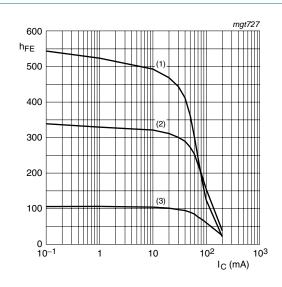
(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 4. BCV61A: Base-emitter saturation voltage as a function of collector current; typical values

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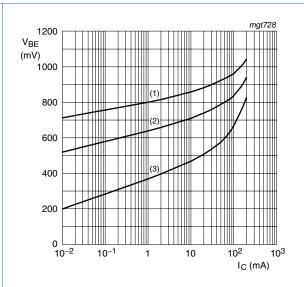
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 5. BCV61B: DC current gain as a function of collector current; typical values



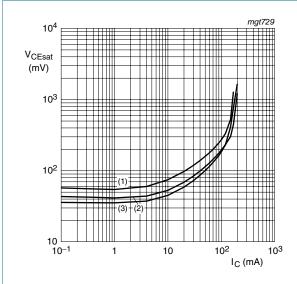
$$V_{CE} = 5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 6. BCV61B: Base-emitter voltage as a function of collector current; typical values

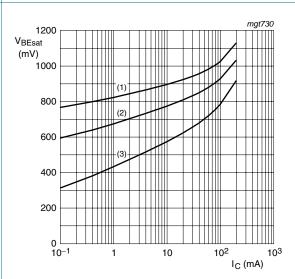


$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. BCV61B: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

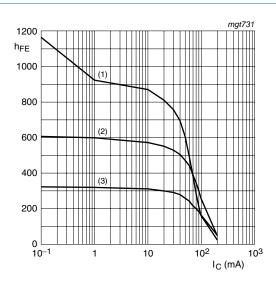
(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 8. BCV61B: Base-emitter saturation voltage as a function of collector current; typical values

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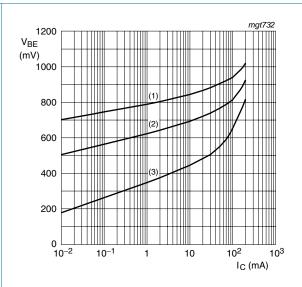
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. BCV61C: DC current gain as a function of collector current; typical values



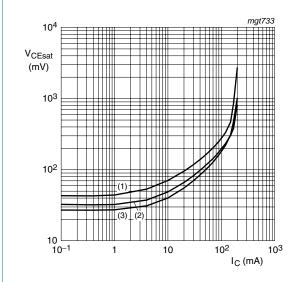
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. BCV61C: Base-emitter voltage as a function of collector current; typical values

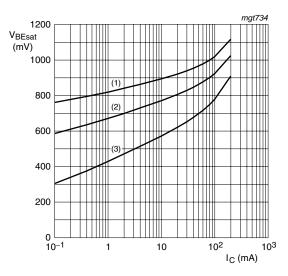


$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. BCV61C: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

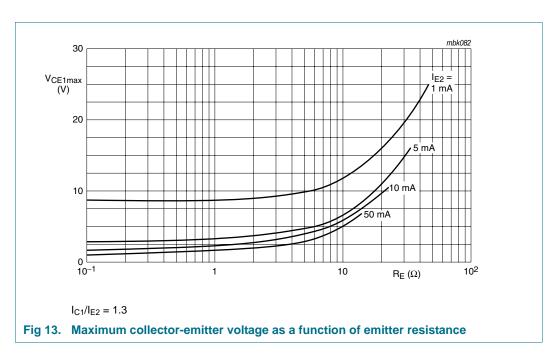
(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

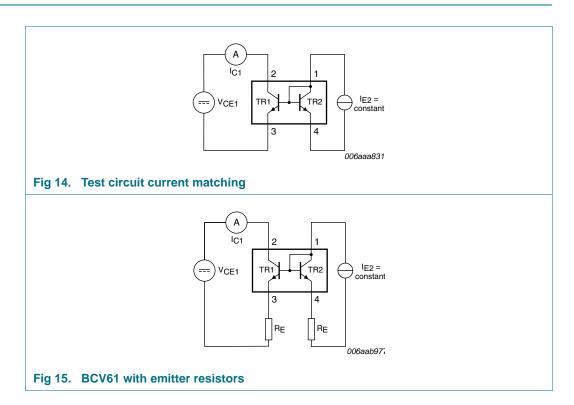
Fig 12. BCV61C: Base-emitter saturation voltage as a function of collector current; typical values

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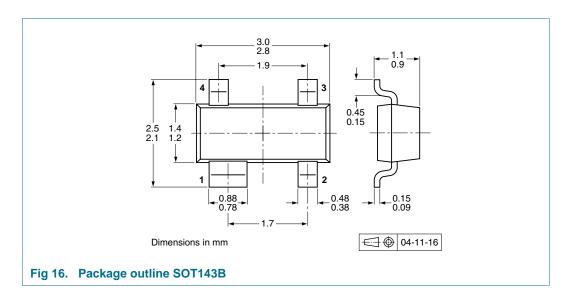


8. Test information



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9. Package outline



10. Packing information

Table 8. Packing methods

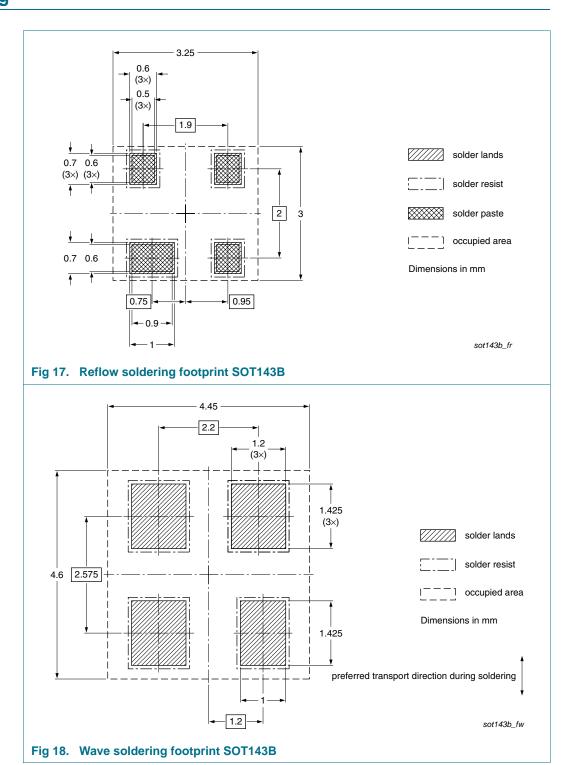
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	ckage Description		Packing quantity		
			3000	10000		
BCV61	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235		
BCV61A						
BCV61B						
BCV61C	_					

^[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BCV61_4	20091218	Product data sheet	-	BCV61_3	
Modifications:		f this data sheet has been red NXP Semiconductors.	designed to comply w	ith the new identity	
	 Legal texts h 	ave been adapted to the new	company name whe	re appropriate.	
	 Section 3 "Or 	rdering information": added			
	Section 4 "Marking": updated				
	• <u>Figure 1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11</u> and <u>12</u> : added				
	 Section 8 "Te 	est information": added			
	• <u>Figure 16</u> : su	perseded by minimized pack	age outline drawing		
	 Section 10 "F 	Packing information": added			
	 Section 11 "S 	Soldering": added			
	 Section 13 "L 	<u>egal information"</u> : updated			
BCV61_3	19990408	Product specification	-	BCV61_CNV_2	
BCV61_CNV_2	19970616	Product specification	-	-	

NPN general-purpose double transistors

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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